

## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
30	0.0042 at V <sub>GS</sub> = 10 V	25	27
	0.0057 at V <sub>GS</sub> = 4.5 V	22	

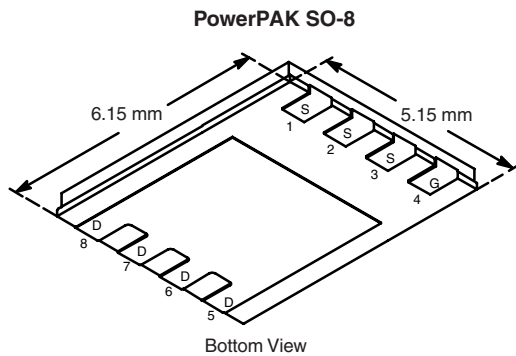
### FEATURES

- Halogen-free available
- TrenchFET<sup>®</sup> Power MOSFET
- New Low Thermal Resistance PowerPAK<sup>®</sup> Package with Low 1.07 mm Profile
- Low Gate Charge
- 100 % R<sub>g</sub> Tested

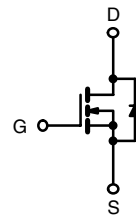


### APPLICATIONS

- Synchronous Rectifier



**Ordering Information:** Si7892BDP-T1-E3 (Lead (Pb)-free)  
Si7892BDP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30		V	
Gate-Source Voltage	V <sub>GS</sub>	± 20			
Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	25	15	A
		T <sub>A</sub> = 70 °C	20	12	
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	60			
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	4.1	1.5		
Avalanche Current	I <sub>AS</sub>	40		mJ	
Single Pulse Avalanche Energy		E <sub>AS</sub>	80		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	5	1.8	W
		T <sub>A</sub> = 70 °C	3.2	1.1	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) <sup>b, c</sup>		260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	20	25	°C/W
	Steady State		53	70	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	2.1	3.2	

**Notes:**

- Surface Mounted on 1" x 1" FR4 board.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

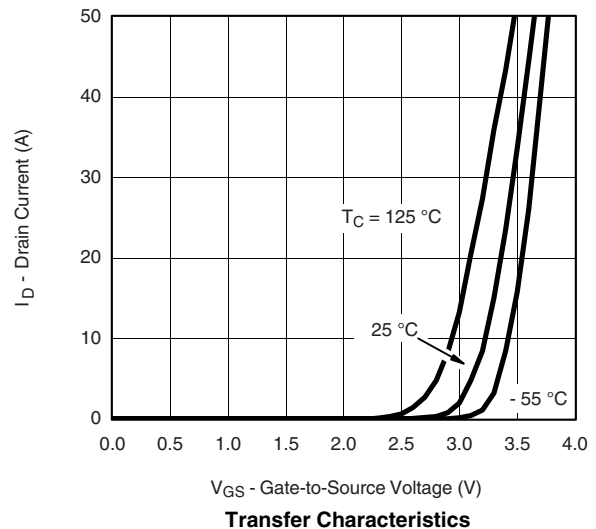
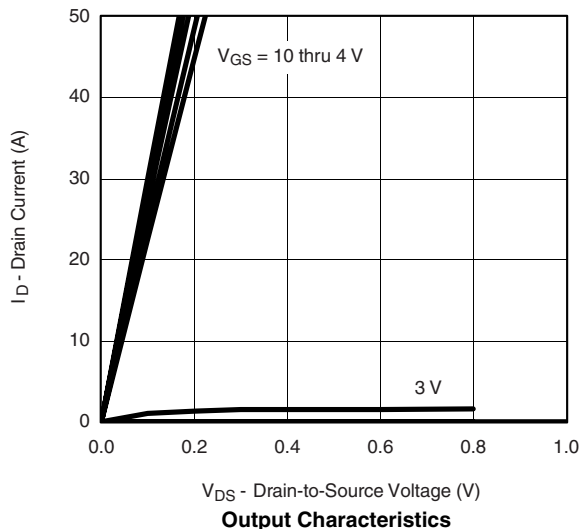
SPECIFICATIONS $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0		3.0	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\ \mu\text{A}$		28		$\text{mV}/^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.5		
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
		$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 10\ \text{V}$	30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 25\ \text{A}$		0.0034	0.0042	$\Omega$
		$V_{GS} = 4.5\ \text{V}, I_D = 22\ \text{A}$		0.0047	0.0057	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\ \text{V}, I_D = 25\ \text{A}$		85		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 4.5\ \text{A}, V_{GS} = 0\ \text{V}$		0.75	1.2	V
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\ \text{V}, V_{SS} = 0\ \text{V}, f = 1\ \text{Hz}$		3775		$\text{pF}$
Output Capacitance	$C_{oss}$			630		
Reverse Transfer Capacitance	$C_{rss}$			295		
Total Gate Charge	$Q_g$	$V_{DS} = 15\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 25\ \text{A}$		27	40	$\text{nC}$
Gate-Source Charge	$Q_{gs}$			11.4		
Gate-Drain Charge	$Q_{gd}$			8.1		
Gate Resistance	$R_g$		0.5	1.2	2.0	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}, R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 10\ \text{V}, R_G = 6\ \Omega$		20	30	$\text{ns}$
Rise Time	$t_r$			13	20	
Turn-Off Delay Time	$t_{d(off)}$			62	100	
Fall Time	$t_f$			20	35	
Source-Drain Reverse Recovery	$t_{rr}$	$I_F = 2.9\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		40	60	$\text{ns}$
Reverse Recovery Charge	$Q_{rr}$			40	60	

Notes:

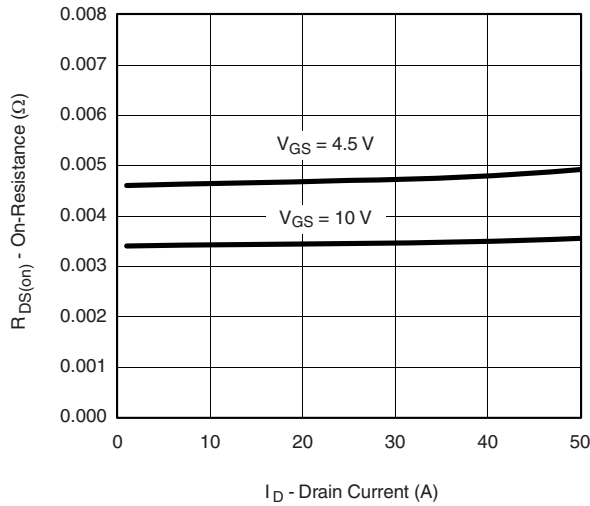
- a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

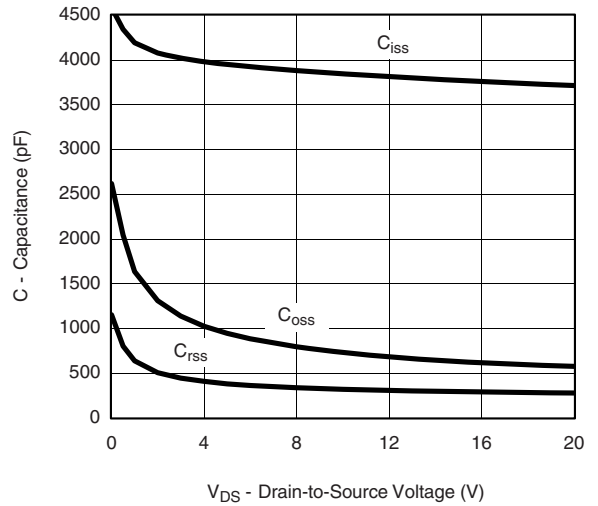
**TYPICAL CHARACTERISTICS**  $25^\circ\text{C}$ , unless otherwise noted



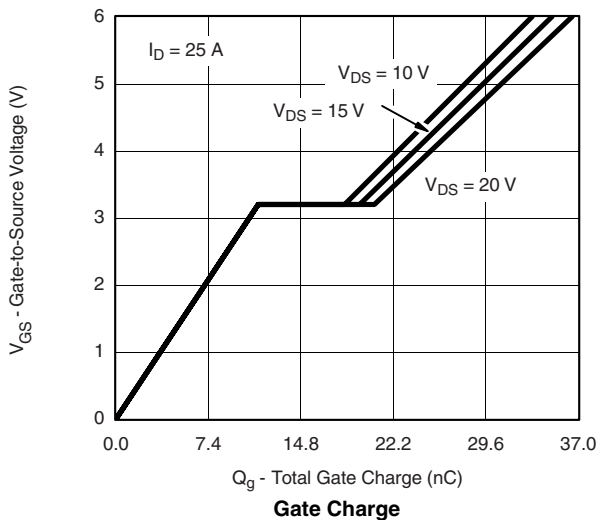
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



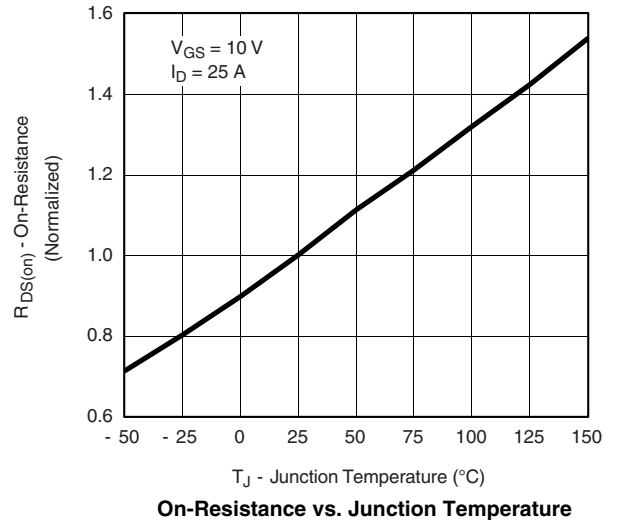
**On-Resistance vs. Drain Current**



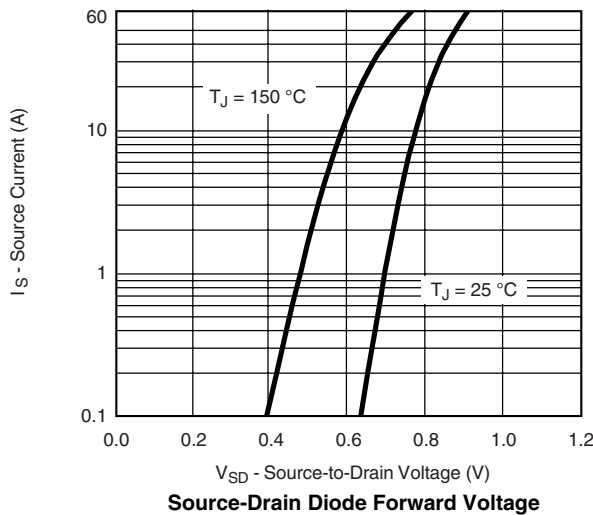
**Capacitance**



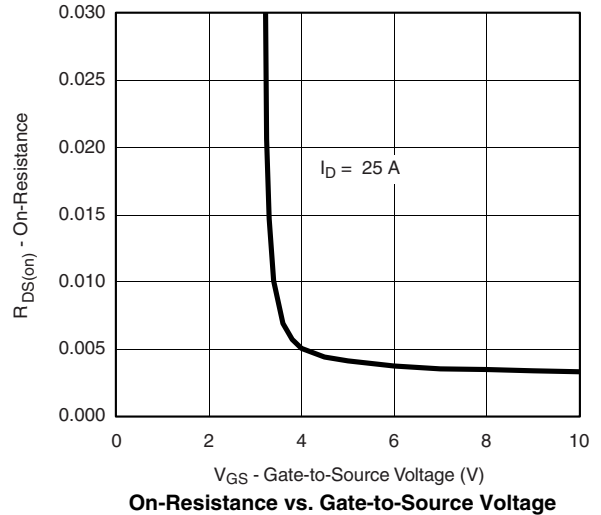
**Gate Charge**



**On-Resistance vs. Junction Temperature**

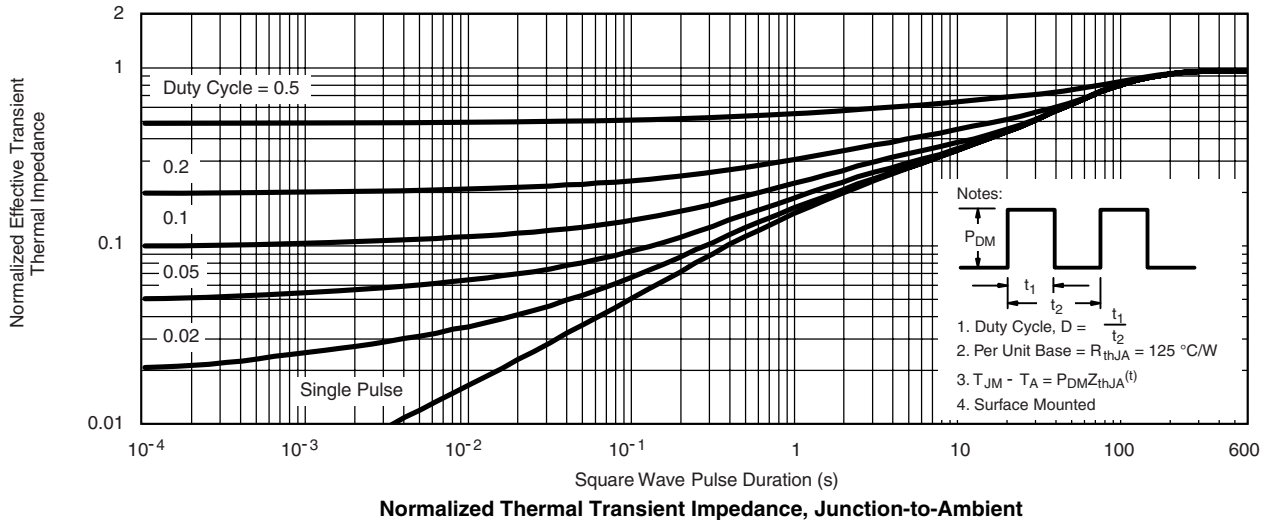
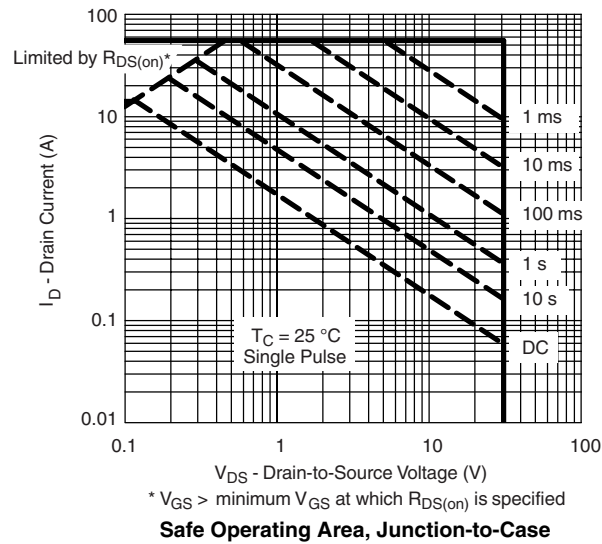
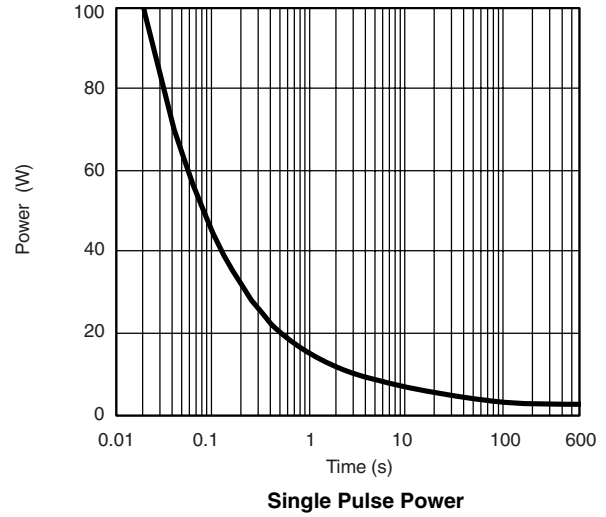
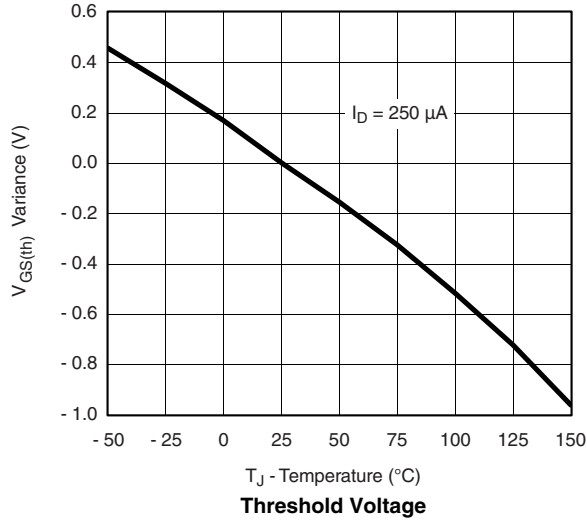


**Source-Drain Diode Forward Voltage**

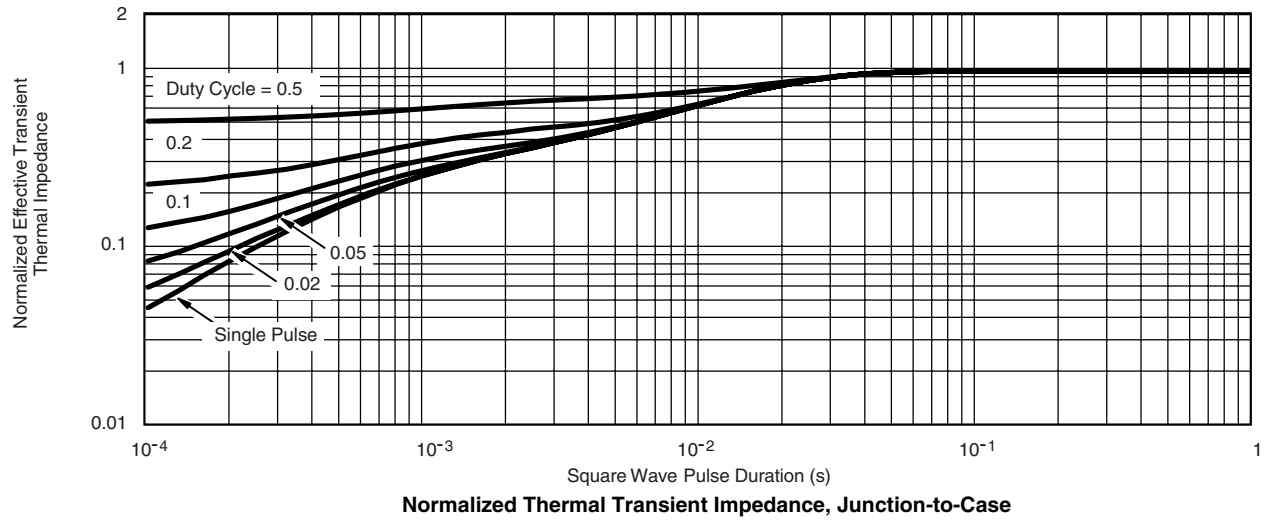


**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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